

# P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V <sub>DS</sub> (V)	-40		
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0120		
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0175		
Q <sub>g</sub> typ. (nC)	74.3		
I <sub>D</sub> (A) <sup>d</sup>	-42		
Configuration	Single		

#### **FEATURES**

- TrenchFET® Gen IV p-channel power MOSFET
- Maximum 175 °C junction temperature

• 100 % R<sub>g</sub> and UIS tested

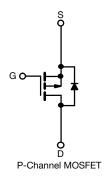
• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE

# **APPLICATIONS**

- Motor drive control
- · LED backlighting
- · Load switch
- Industrial



ORDERING INFORMATION		
Package	TO-252	
Lead (Pb)-free and halogen-free	SUD40151EL-GE3	

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	-40	V
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain august	T <sub>C</sub> = 25 °C		-42 <sup>d</sup>	
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-28.6	
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	-100	А
Continuous source-drain diode current		I <sub>S</sub>	-41.7	
Single pulse avalanche current a	L = 0.1 mH	I <sub>AS</sub>	-25	
Single pulse avalanche energy <sup>a</sup>	L = 0.1 mm	E <sub>AS</sub>	31.25	mJ
Marrian and a substitution	T <sub>C</sub> = 25 °C	_	50 b	W
Maximum power dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	16.7 b	VV
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	.0
Soldering recommendations (peak temperature) c			260	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) <sup>c</sup>		R <sub>thJA</sub>	60	°C/W
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	3	C/VV

#### Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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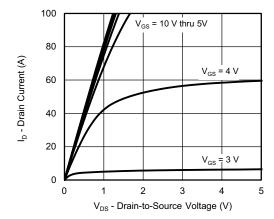
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•		•		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-40	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1.5	=	-2.5	V	
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	250	nA	
		$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	-150	μA	
		V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	-5	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -10 \text{ V}, V_{GS} = -10 \text{ V}$	-30	-	-	Α	
Participant and the state of th	_	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -17.5 A	-	0.0100	0.0120	Ω	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -14.5 A	-	0.0135	0.0175		
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -17.5 \text{ A}$	-	70	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	5340	-	pF	
Output capacitance	C <sub>oss</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	335	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	303	-		
Total gate charge	Qg		-	74.3	112	nC	
Gate-source charge	$Q_{gs}$	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -17.5 \text{ A}$	-	12.7	-		
Gate-drain charge	$Q_{gd}$		-	11.1	-		
Gate resistance	$R_g$	f = 1 MHz	0.86	4.3	8.6	Ω	
Turn-on delay time	t <sub>d(on)</sub>		-	15	30		
Rise time	t <sub>r</sub>	$V_{DD} = -20 \text{ V}, R_L = 1.4 \Omega, I_D \cong -14 \text{ A},$	-	10	20	no	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	75	113	ns	
Fall time	t <sub>f</sub>		-	75	113		
<b>Drain-Source Body Diode Characteristi</b>	cs						
Pulse diode forward current (t = 100 μs)	I <sub>SM</sub>		-	-	-42	Α	
Body diode voltage	$V_{SD}$	I <sub>F</sub> = -14 A, V <sub>GS</sub> = 0 V	-	-0.85	-1.5	V	
Body diode reverse recovery time	t <sub>rr</sub>		-	30	45	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = -14 A, di/dt = 100 A/μs	_	0.02	0.04	μC	
Reverse recovery fall time	t <sub>a</sub>	i <sub>F</sub> = -14 A, αι/αι = 100 A/μS	_	15.3	-		
Reverse recovery rise time	t <sub>b</sub>		-	14.7	-	ns	
Body diode peak reverse recovery charge	I <sub>RM(REC)</sub>		-	-	2.8	Α	

## Notes

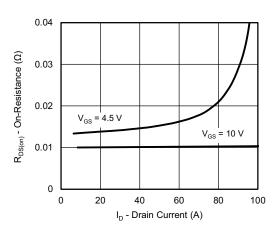
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

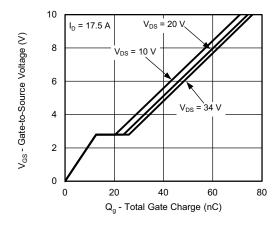




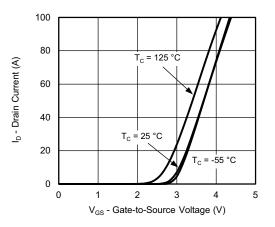
#### **Output Characteristics**



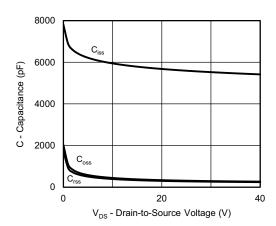
On-Resistance vs. Drain Current and Gate Voltage



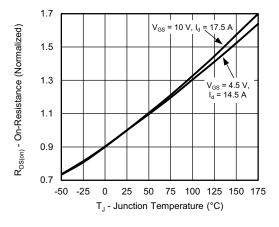
**Gate Charge** 



**Transfer Characteristics** 

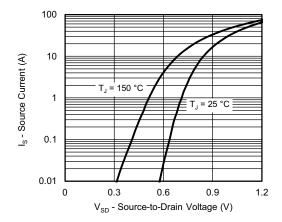


Capacitance

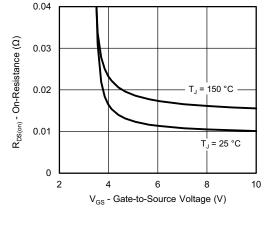


On-Resistance vs. Junction Temperature

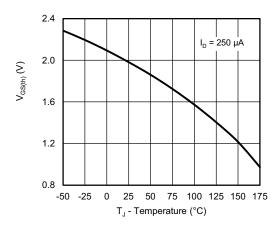




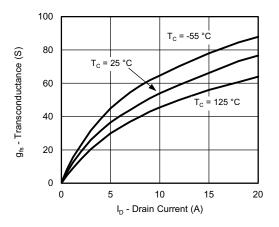
Source-Drain Diode Forward Voltage



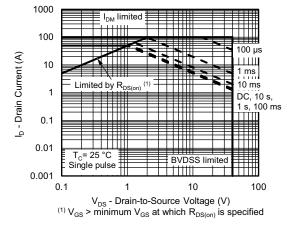
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

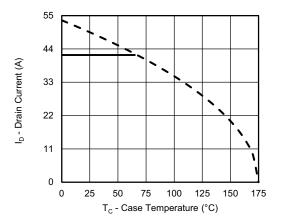


Transconductance

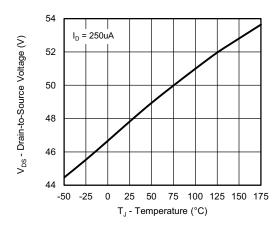


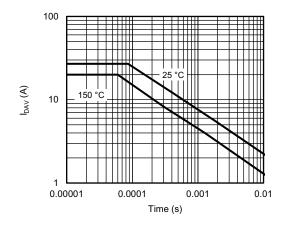
Safe Operating Area, Junction-to-Ambient





## Current Derating a





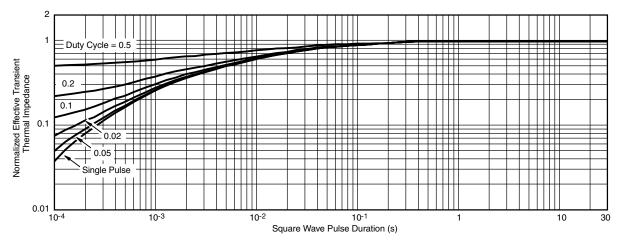
Drain Source Breakdown vs. Junction Temperature

I<sub>DAV</sub> vs. Time

#### Note

a. The power dissipation  $P_D$  is based on  $T_J$  max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





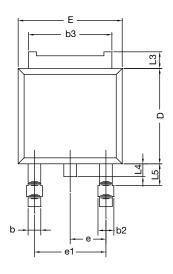
Normalized Thermal Transient Impedance, Junction-to-Case

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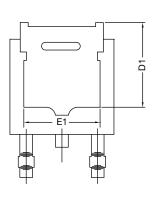


TO-252AA Case Outline

## **VERSION 1: FACILITY CODE = Y**







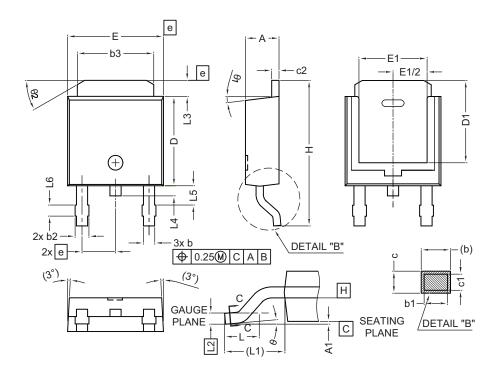
	MILLIMETERS		
DIM.	MIN.	MAX.	
A	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
Е	6.35	6.73	
E1	4.32	-	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	- 1.02		
L5	1.01	1.52	

#### Note

• Dimension L3 is for reference only



## **VERSION 2: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21 -		
E	6.35 6.73		
E1	4.32 -		
е	2.29 BSC		
Н	9.94 10.34		

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ł ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25° 35°		

## Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019

DWG: 5347



# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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